

N-Ch MOSFET

General Description

The WSR140N12 is the highest performance trench N-ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSR140N12 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

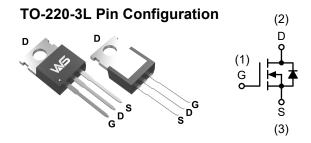
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BV _{DSS}	R _{DSON}	I _D
120V	5mΩ	140A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	±20	V
I _D	Continuous Drain Current, V _{GS} @ 10V(T _C =25 °C)	140	А
I _{DM}	Pulsed Drain Current	330	Α
EAS	Single Pulse Avalanche Energy	400	mJ
P _D	Total Power Dissipation _C =25 [℃])	192	W
RθJA	Thermal resistance, junction-ambient	62	°C/W
RθJC	Thermal resistance, junction-case	0.65	°C/W
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$
TJ	Operating Junction Temperature Range	-55 to 150	°C



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	120			V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =30A		5.0	6.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS} , I_D =250uA	2.0	3.0	4.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =120V , V _{GS} =0V , T _J =25℃			1	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
Q_g	Total Gate Charge			68.9		nC
Q _{gs}	Gate-Source Charge	V_{DS} =50V , V_{GS} =10V , I_{D} =15A		18.1		
Q_{gd}	Gate-Drain Charge			15.9		
T _{d(on)}	Turn-On Delay Time	\/ -50\/ \/ -40\/		30.3		
T _r	Rise Time	- V _{DD} =50V , V _{GS} =10V - R _G =2Ω, - I _D =25A		33.0		no
$T_{d(off)}$	Turn-Off Delay Time			11.7		ns
T _f	Fall Time	- 10-23A		59.5		
C _{iss}	Input Capacitance			5823		
Coss	Output Capacitance	V_{DS} =50V , V_{GS} =0V , f=1MHz		778.3		pF
C _{rss}	Reverse Transfer Capacitance			17.5		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	\\ -\\ -0\\			150	Α
I _{SM}	Pulsed Source Current ^{2,6}	V _G =V _D =0V , Force Current			330	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =25A , T _J =25℃			1.3	V

■ Note

- ${\bf 1}$) Repetitive rating; pulse width limited by max. junction temperature.
- 2) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 3) The value of R0JA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.
- 4) VDD=50 V, RG=50 $\Omega,$ L=0.3 mH, starting Tj=25 °C.
- ⁵) Calculated continuous current based on maximum allowable junction temperature.



Typical Operating Characteristics

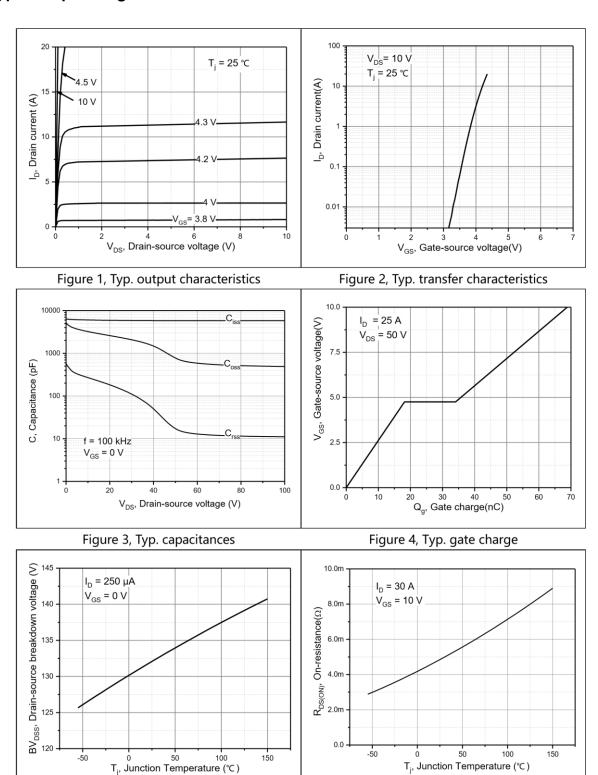
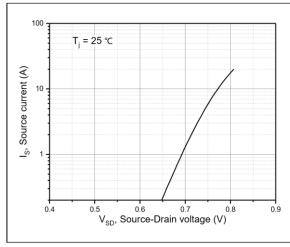


Figure 5, Drain-source breakdown voltage

Figure 6, Drain-source on-state resistance



Typical Operating Characteristics



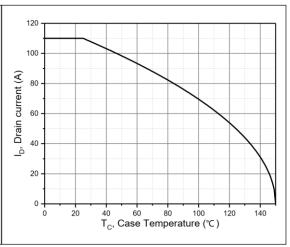


Figure 7, Forward characteristic of body diode

Figure 8, Drain current

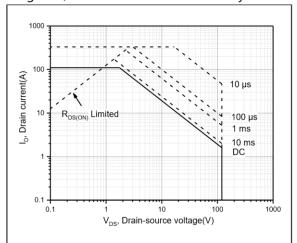
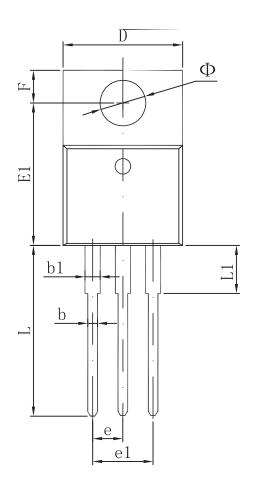


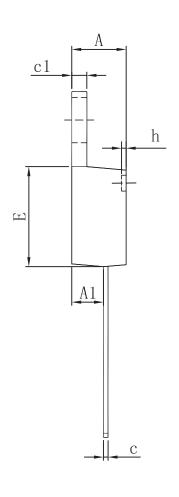
Figure 9, Safe operation area T_C=25 ℃



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Packaging information





Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
A	4.470	4.670	0.176	0.184	
A1	2.520	2.820	0.099	0.111	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
Е	8.500	8.900	0.335	0.350	
E1	12.060	12.460	0.475	0.491	
е	2.540 TYP		0.100	TYP	
e1	4.980	5. 180	0.196	0.204	
F	2.590	2.890	0.102	0.114	
h	0.000	0.300	0.000	0.012	
L	13.400	13.800	0.528	0.543	
L1	3.560	3.960	0.140	0.156	
Ф	3.735	3. 935	0.147	0. 155	



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